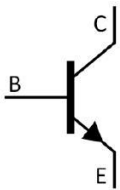


Silicon NPN transistor in a TO-92 Plastic Package.

High gain, good linearity of h_{FE} .

TV final picture IF amplifier applications.

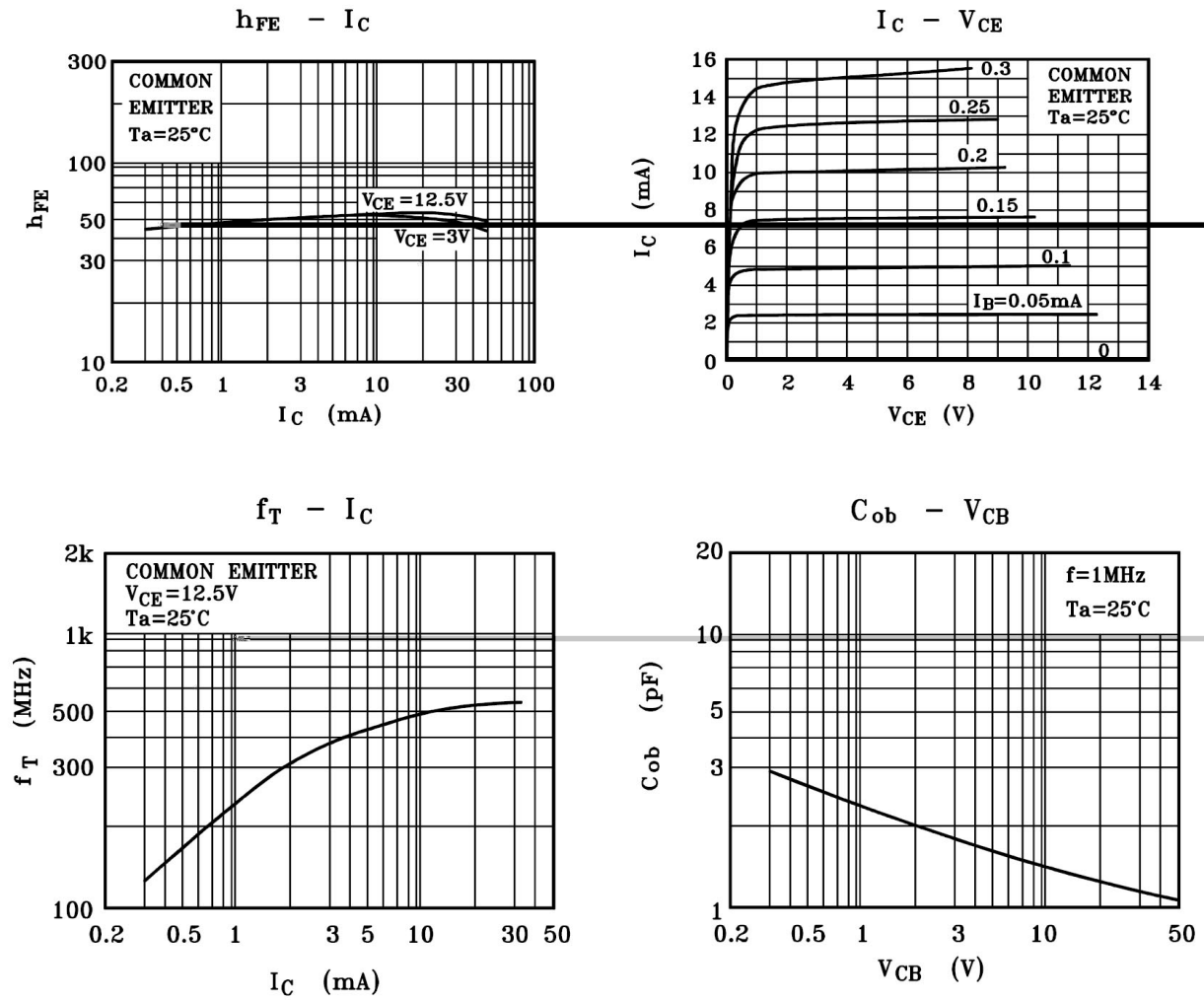


PIN1 Collector PIN 2 Emitter PIN 3 Base

See Marking Instructions.

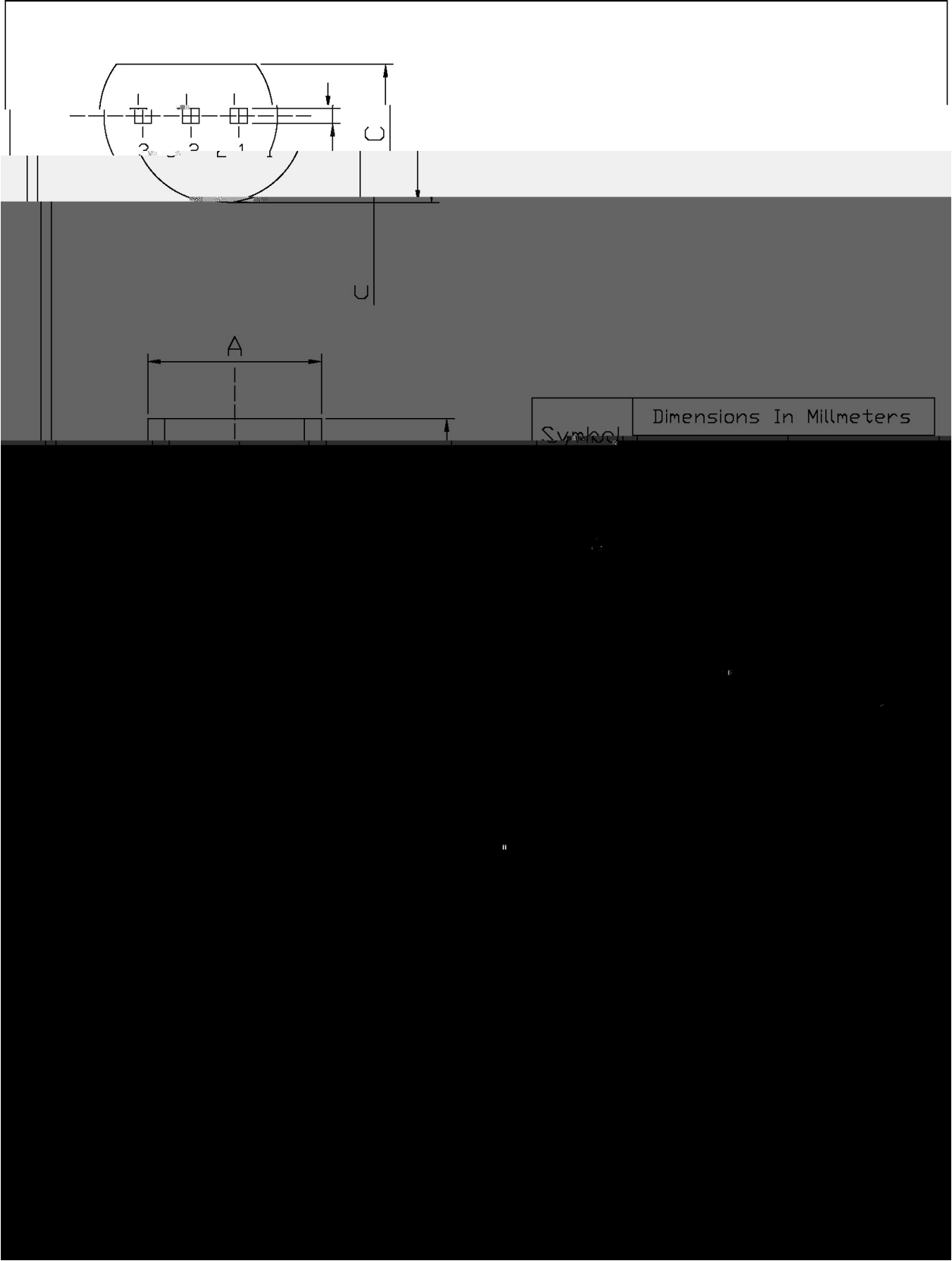
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	30	V
Collector to Emitter Voltage	V_{CEO}	25	V
Emitter to Base Voltage	V_{EBO}	4.0	V
Collector Current - Continuous	I_C	50	mA
Emitter Current - Continuous	I_E	-50	mA
Collector Power Dissipation	P_C	300	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55~150	

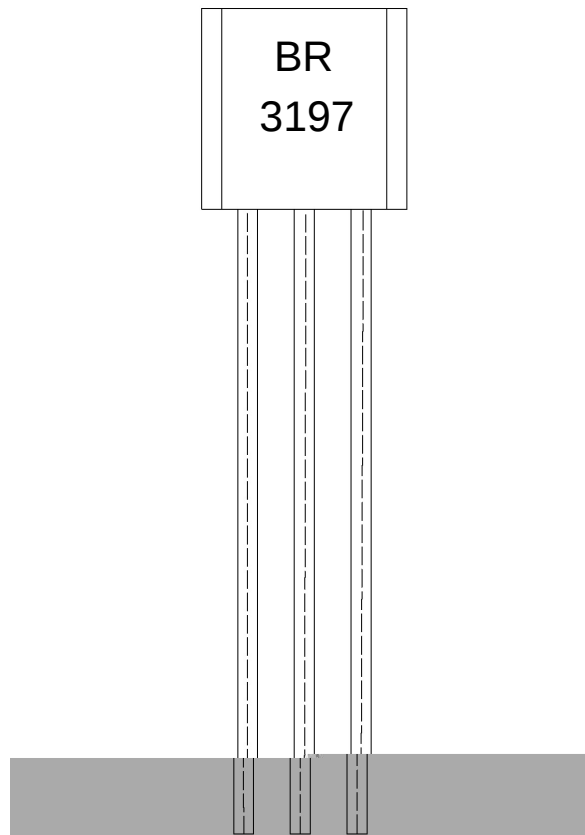
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=10mA$ $I_B=0$	25			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=30V$ $I_E=0$			0.1	A
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=3.0V$ $I_C=0$			0.1	A
DC Current Gain	h_{FE}	$V_{CE}=12.5V$ $I_C=12.5mA$	40		240	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=15mA$ $I_B=1.5mA$			0.2	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=15mA$ $I_B=1.5mA$			1.5	V
Transition Frequency	f_T	$V_{CE}=12.5V$ $I_C=12.5mA$	300			MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=10V$ $f=30MHz$ $I_E=0$	0.8		2.0	pF
Reverse Transfer Capacitance	C_{re}	$V_{CC}=12.5V$ $f=45MHz$ $I_E=-12.5mA$	28		36	dB
Collector- Base Time Constant	$C_c \cdot r_{bb'}$	$V_{CB}=10V$ $f=30MHz$ $I_E=-1.0mA$			25	ps



T0-92

Unit: mm



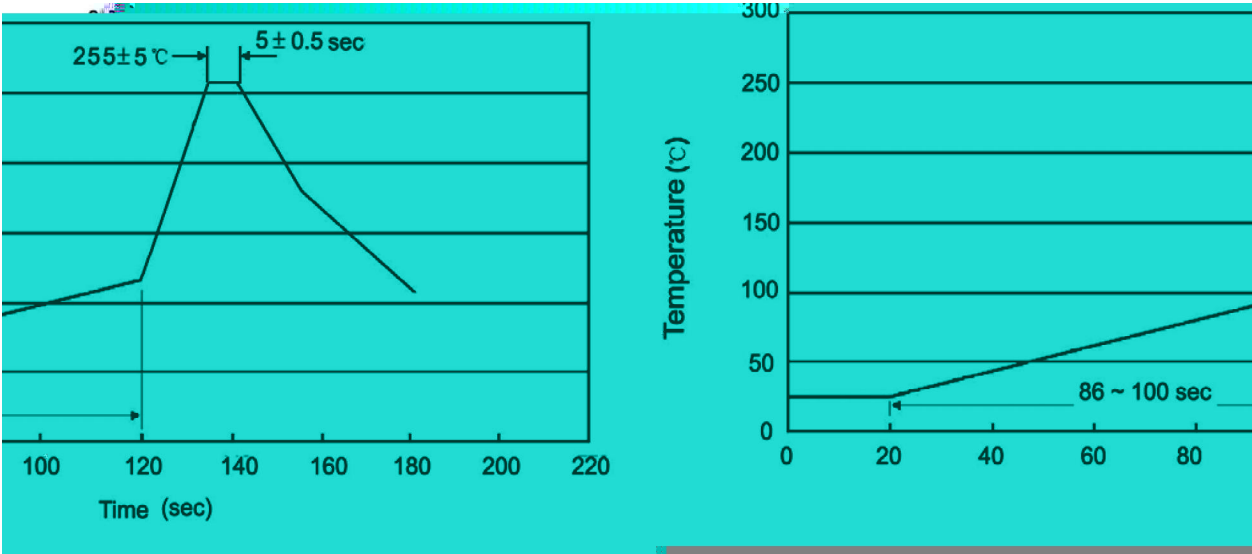


Note:

BR: Company Code.

3197: Product Type.

***: Lot No. Code,code change with Lot No.



Note:

- 1

25 150

60 90sec;
- 2

255 5

5 0.5sec;
- 3

2 10 /sec.
- 1.Preheating:25~150 , Time:60~90sec.

2.Peak Temp.:255 5 , Duration:5 0.5sec.

3. Cooling Speed: 2~10 /sec.

270 5

10 1 sec.

Temp:270±5

Time:10±1 sec

/ BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm3)		
	只 袋	袋 盒	只 盒	盒 箱	只 箱	袋	盒	箱

/ AMMO

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm3)	
	只 纸带	纸带 盒	纸带层 盒	盒 箱	只 箱	盒	箱
							小箱 , 大箱